

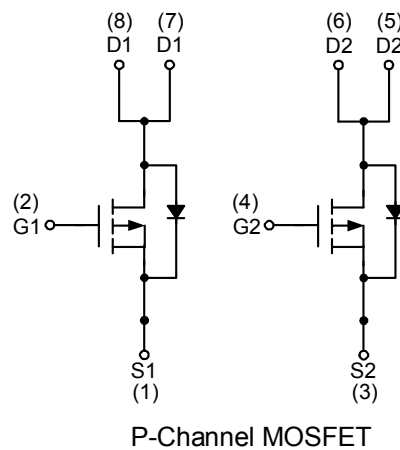
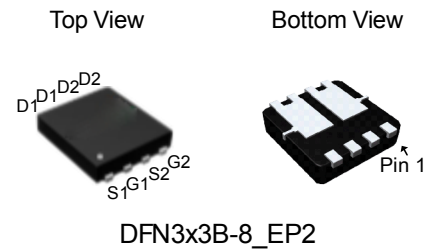
Features

- -30V/-15A,
 $R_{DS(ON)} = 20m\Omega$ (typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 25m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

Applications

- Pico-Projector.

Pin Description



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	-2	A
I _D	Continuous Drain Current	T _C =25°C	-15	A
		T _C =100°C	-10	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-60	
P _D	Maximum Power Dissipation	T _C =25°C	12.5	W
		T _C =100°C	5	
R _{θJC}	Thermal Resistance-Junction to Case		10	°C/W
I _D	Continuous Drain Current	T _A =25°C	-4.9	A
		T _A =70°C	-3.9	
P _D ^c	Maximum Power Dissipation	T _A =25°C	1.2	W
		T _A =70°C	0.76	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	Steady state	105	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	-11	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	30	mJ

Note a Pulse width limited by max. junction temperature.

Note b UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J = 25^\circ\text{C}$).

Note c Surface Mounted on 1in^2 pad area.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

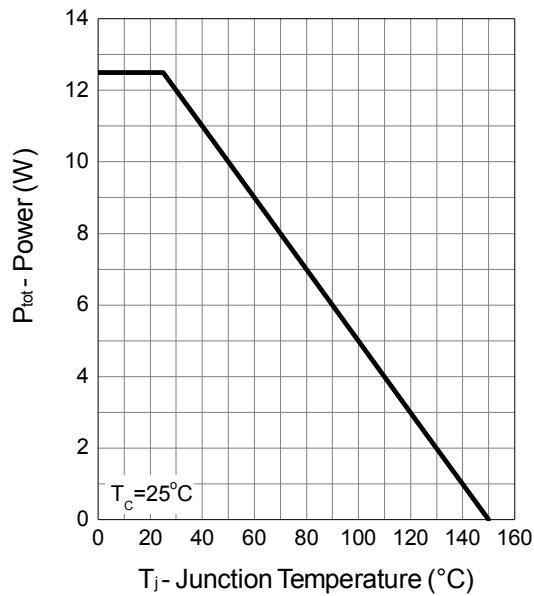
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =85°C	-	-	-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.3	-1.8	-2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-7A V _{GS} =-4.5V, I _{DS} =-4A	- -	20 25	22 32	mΩ mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-7A, dI _{SD} /dt=100A/μs	-	20	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	12	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz	-	750	975	pF
C _{oss}	Output Capacitance		-	142	-	
C _{rss}	Reverse Transfer Capacitance		-	102	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =15Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =1Ω	-	9	16	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	55	99	
t _f	Turn-off Fall Time		-	34	61	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _{DS} =-7A	-	8	-	nC
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _{DS} =-7A	-	17	24	
Q _{gs}	Gate-Source Charge		-	2	-	
Q _{gd}	Gate-Drain Charge		-	4	-	

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

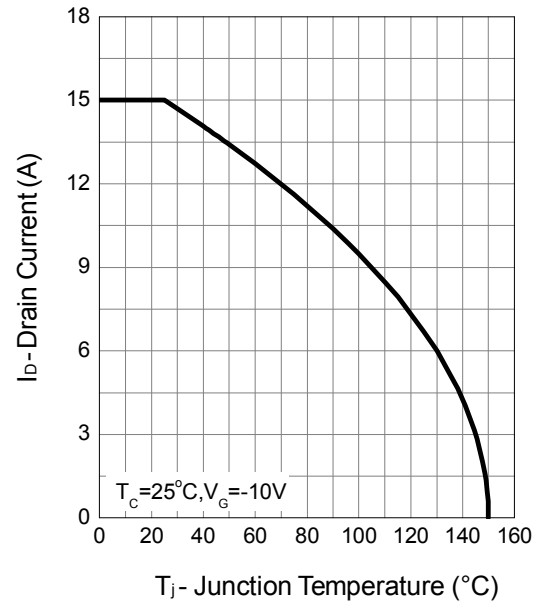
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

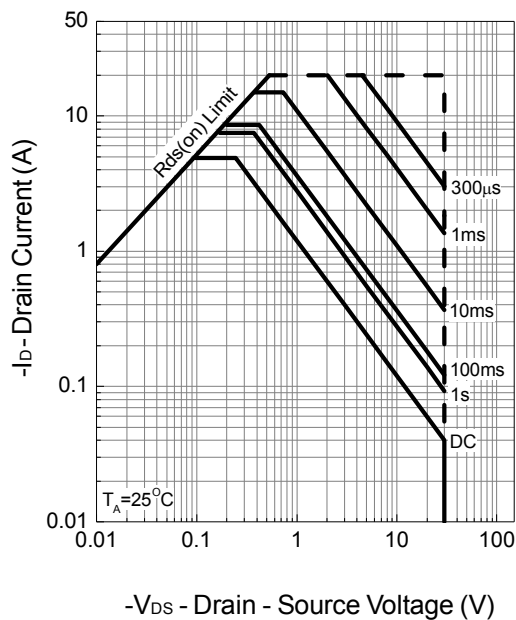
Power Dissipation



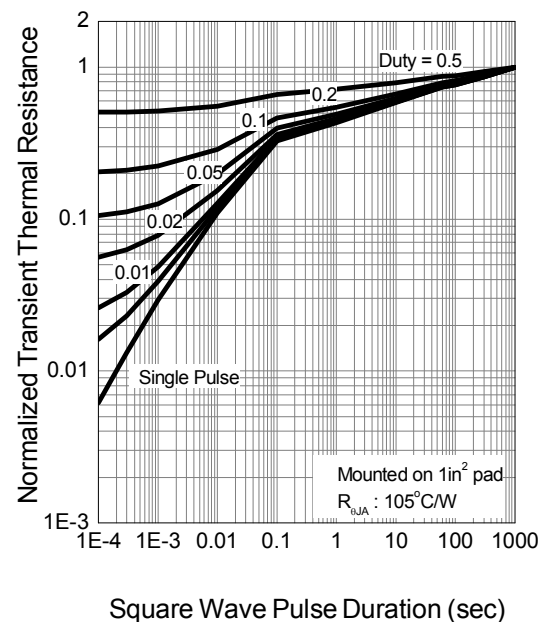
Drain Current



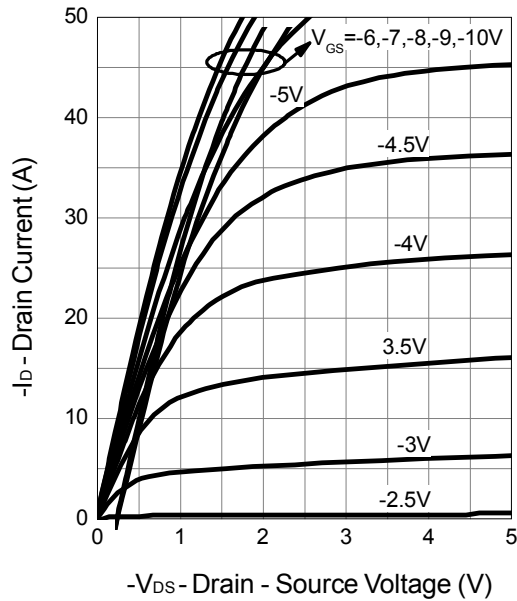
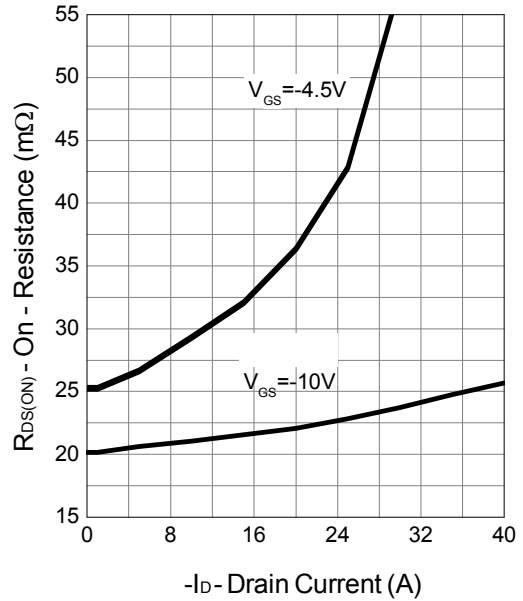
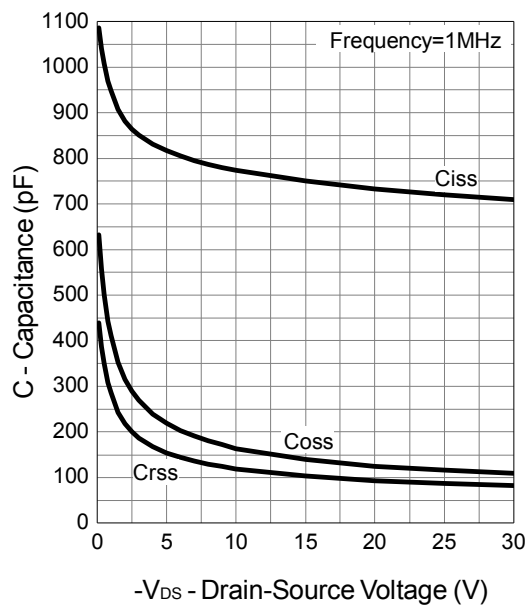
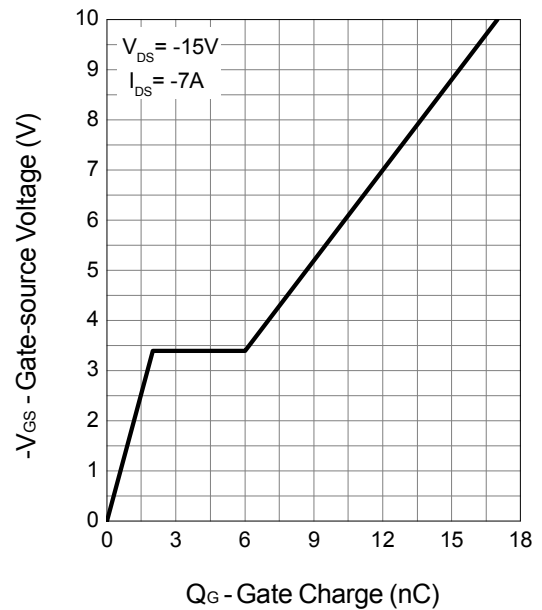
Safe Operation Area



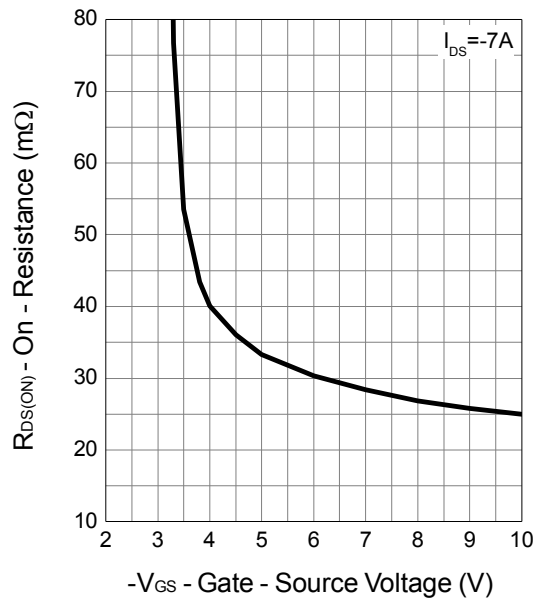
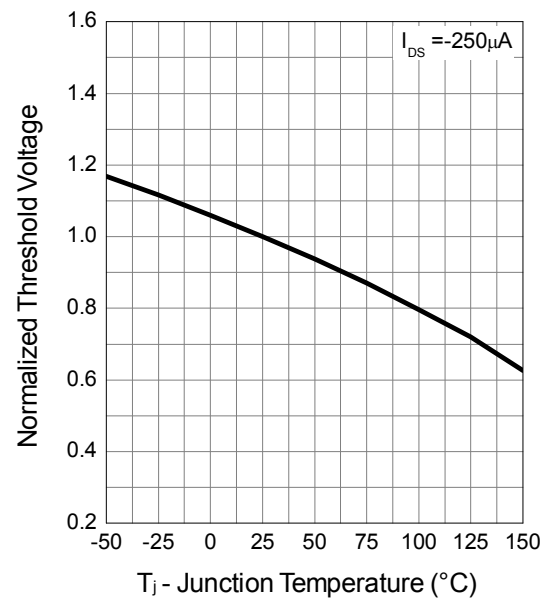
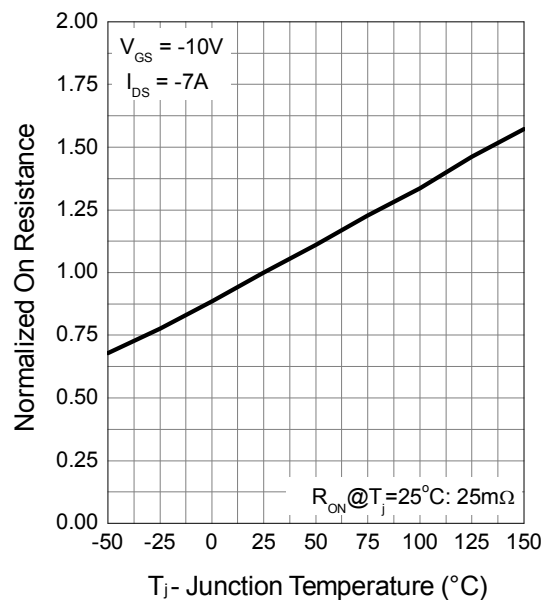
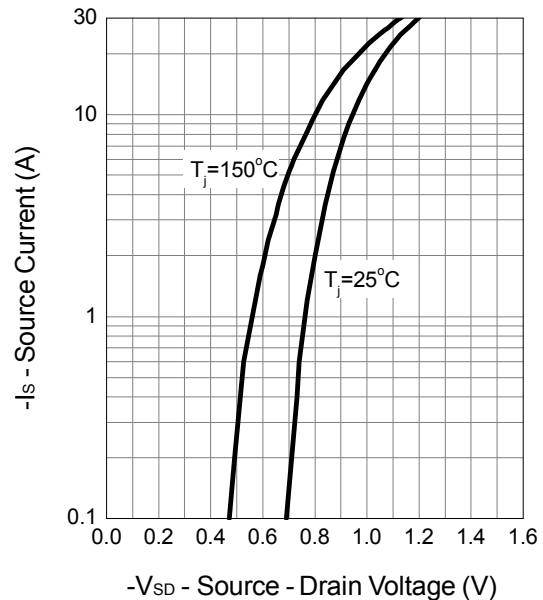
Thermal Transient Impedance



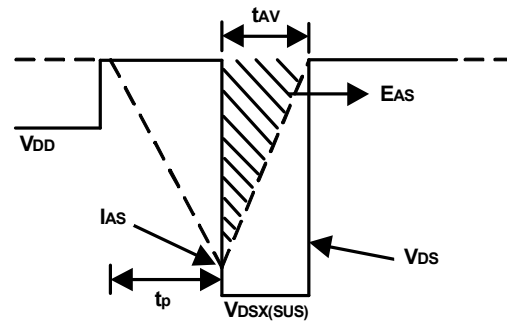
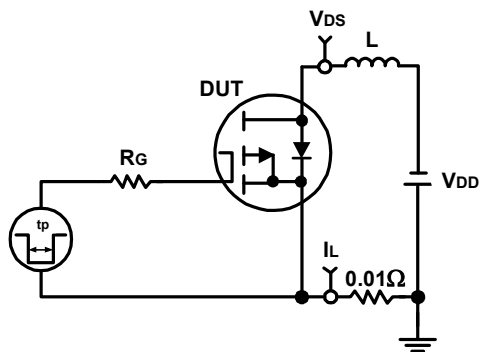
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Capacitance

Gate Charge


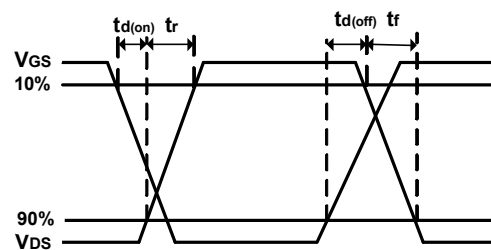
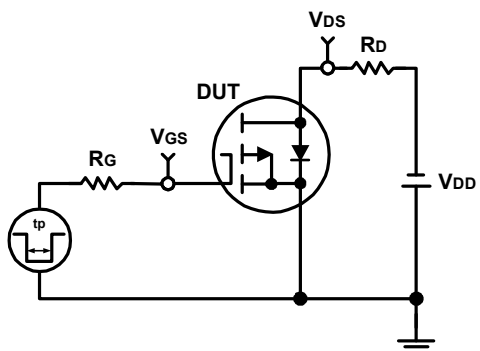
Typical Operating Characteristics (Cont.)

Gate-Source On Resistance

Gate Threshold Voltage

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

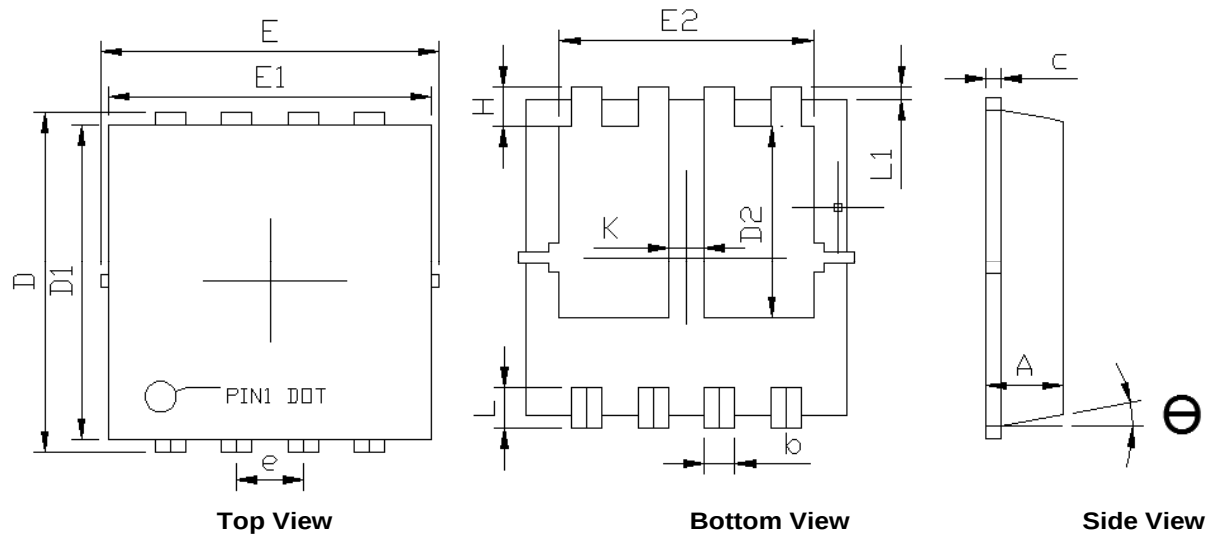


Switching Time Test Circuit and Waveforms



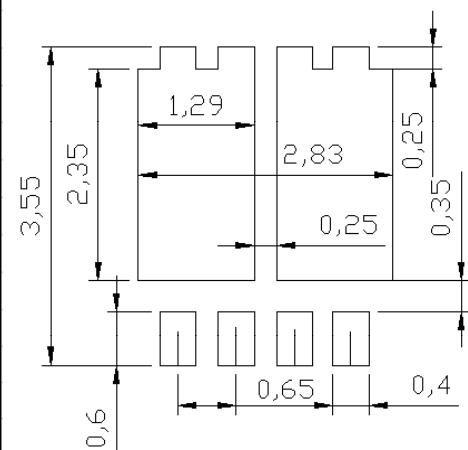
Package Information

DFN3.3x3.3-8L_EP2_P



SYMBOLS	DFN3.3x3.3G-8_EP2_P			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	0.80	0.028	0.031
b	0.25	0.35	0.010	0.014
c	0.10	0.25	0.004	0.010
D	3.25	3.45	0.128	0.136
D1	3.00	3.20	0.118	0.126
D2	1.78	1.98	0.070	0.078
E	3.20	3.40	0.126	0.134
E1	3.00	3.20	0.118	0.126
E2	2.39	2.59	0.094	0.102
e	0.65BSC		0.026 BSC	
H	0.30	0.50	0.012	0.020
L	0.30	0.50	0.012	0.020
L1	0.13 REF		0.005 REF	
K	0.30	-	0.012	-
θ	-	12°	-	12°

RECOMMENDED LAND PATTERN



UNIT: mm